

Abstract

In a semiconductor system 20 made up of multiple sublayers 1, 2, 3, 4, a sublayer 4 over the largest part of a cross-sectional area BC in the interior of the semiconductor system 5 20 borders immediately on the first sublayer 2, while bordering on a second sublayer 1 only in a comparatively narrow edge region of the cross-sectional area BC. The semiconductor system is characterized by a low bulk resistance and a high breakdown voltage in the edge region. In addition, 10 a method for manufacturing this semiconductor system is specified.

(Figure 2)

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